

HZM6.8ZMFA

Silicon Planar Zener Diode for Surge Absorb

HITACHI

ADE-208-783A(Z)

Rev 1

Nov. 1999

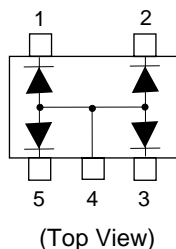
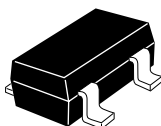
Features

- HZM6.8ZMFA has four devices in a monolithic, and can absorb surge.
- Low capacitance ($C=25\text{pF}$ max) and can protect ESD of signal line.
- MPAK-5 Package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HZM6.8ZMFA	68N	MPAK-5

Outline



- 1 Cathode
- 2 Cathode
- 3 Cathode
- 4 Anode
- 5 Cathode

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Power dissipation	Pd ^{*1}	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note 1. Four device total, See Fig.2.

Electrical Characteristics (Ta = 25°C) ^{*1}

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Zener voltage	V _Z	6.47	—	7.00	V	I _Z = 5 mA, 40ms pulse
Reverse current	I _R	—	—	2	μA	V _R = 3.5V
Capacitance	C	—	—	25	pF	V _R = 0V, f = 1 MHz
Dynamic resistance	r _d	—	—	30	Ω	I _Z = 5 mA
ESD-Capability ^{*2 *3}	—	25	—	—	kV	C = 150pF, R = 330Ω, Both forward and reverse direction 10 pulse

- Notes
1. Per one device.
 2. Failure criterion ; I_R > 2 μA at V_R = 3.5V.
 3. Between cathode and anode.

Main Characteristic

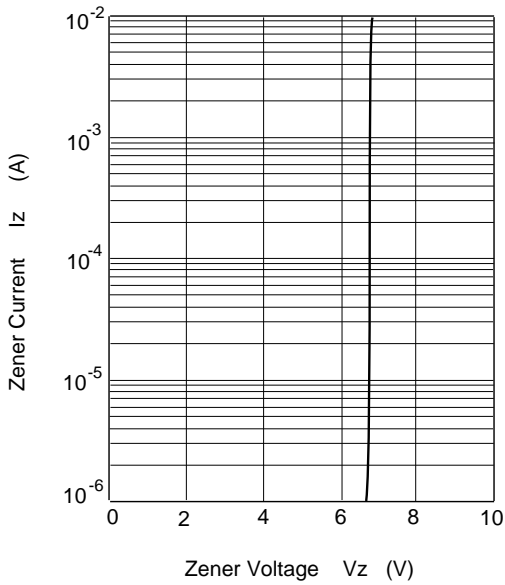


Fig.1 Zener current Vs. Zener voltage

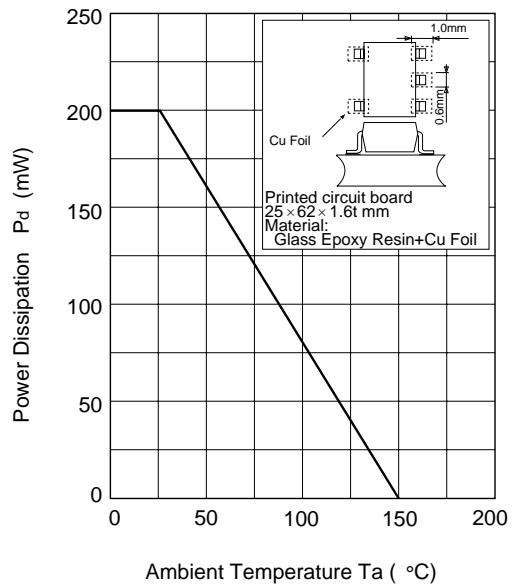


Fig.2 Power Dissipation Vs. Ambient Temperature

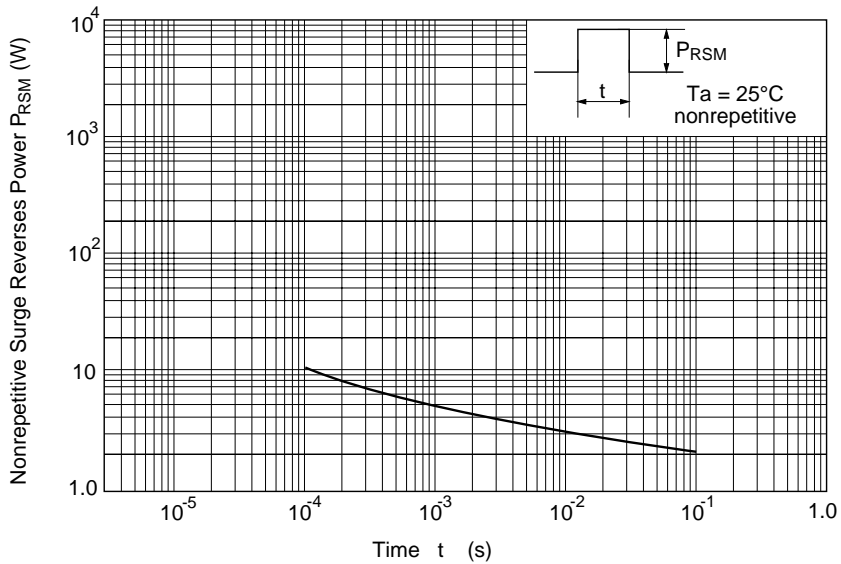


Fig.3 Surge Reverse Power Ratings

Main Characteristic

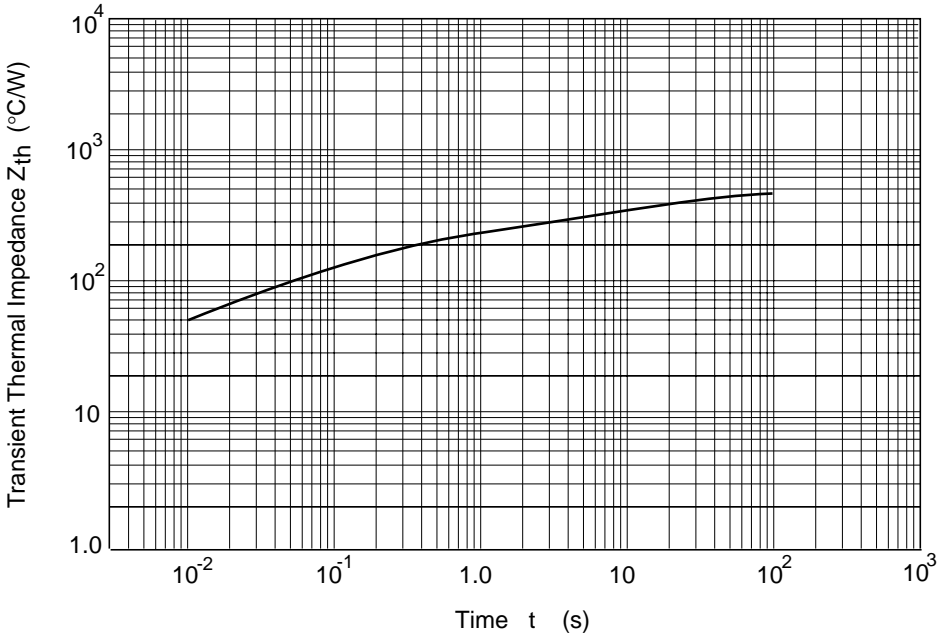
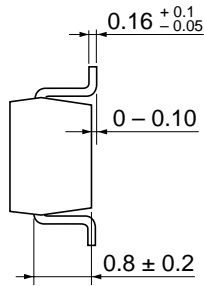
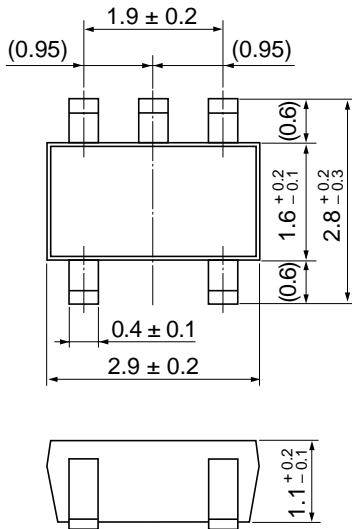


Fig.4 Transient Thermal Impedance

Package Dimensions

Unit: mm



Hitachi Code	MPAK-5
JEDEC	—
EIAJ	—
Mass	0.013 g

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